

D-3213

IN THE UNITED STATES PATENT AND TRADEMARK OFFICEPATENT

In re application of:

Calvez et al.

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Group Art Unit: Unknown

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Serial No. 10/550,846

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Examiner: N/A

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Filed: March 24, 2004 (I.A.)

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For: IMPROVEMENTS IN AND
RELATING TO VERTICAL-
CAVITY SEMICONDUCTOR
OPTICAL DEVICES

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INFORMATION DISCLOSURE STATEMENT

Dear Sir:

Applicant wishes to call to the attention of the Examiner the documents cited on the accompanying Form PTO-1449. No concession is made that these documents are prior art, and applicant expressly reserves the right to antedate the documents as may be appropriate. Applicant requests that each of these documents be made of record in the above-identified application.

Respectfully submitted,



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INFORMATION DISCLOSURE CITATION IN AN APPLICATION (Use several sheets if necessary)		Applicant: Calvez et al.					
		Filing Date: March 24, 2004		Group Art Unit: Unknown			
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						YES	NO
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AF	A. Black, "Wafer Fusion: Materials Issues and Device Results", <i>IEEE Journal Sel. Topics in Quantum Electronics</i> , Vol. 3, No. 3, 1997, p. 943-951.						
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	BI	M.D. Mermelstein et al., "RIN transfer analysis in pump depletion regime for Raman fibre amplifiers", <i>Electronics Letters</i> , Vol. 38, No. 9, 2002, p. 403-405.			
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[illegible]

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BV	Coherent Laser Division. Sapphire Optically Pumped Semiconductor Lasers, Copyright 2002, Coherent, Inc.
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